Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (currently amended): An organic light emitting diode device having comprising: a substrate, a layer of organic light emitting material, a transparent cathode comprising a layer of material with a work function less than 4 eV, a passivation layer comprising boron oxide overlying said cathode, and an encapsulation layer directly overlying said passivation layer.

Claim 2 (canceled).

Claim 3 (currently amended): A device according to claim [2] 1, wherein said material with a work function of less than 4 eV comprises calcium.

Claims 4-8 (canceled).

Claim 9 (currently amended): A method of manufacturing an organic light emitting diode device, comprising the steps of: (a) taking a substrate bearing a layer of organic light emitting material and a transparent cathode comprising a layer of material with a work function less than 4 eV; (b) depositing a passivation layer comprising boron oxide on the device said cathode; and (c) depositing an encapsulating layer directly on said passivation layer.

Claim 10 (original): A method according to claim 9, wherein said passivation layer is deposited by thermal evaporation.

Claims 11-18 (canceled).

Claim 19 (original): A passivation layer for an electronic device, the passivation layer comprising boron oxide.

Claim 20 (currently amended): A device according to claim [2] 1, wherein said light emitting material is a polymeric light emitting material.

Claim 21 (currently amended): A device according to claim [2] 1, wherein said passivation layer directly overlies said layer of material with a work function less than 4 eV.

Claim 22 (canceled).

Claim 23 (currently amended): A device according to claim [22] 1, wherein said encapsulating layer comprises a dielectric oxide selected from a group consisting of Al₂O₃, SiO₂, TiO₂, ZrO₂, MgO, HfO₂, Ta₂O₅, aluminum titanium oxide, and tantalum hafnium oxide.

Claim 24 (previously presented): A device according to claim 1, further comprising sealing layers of adhesive and glass.

Claim 25 (previously presented): A device according to claim 24, wherein said adhesive comprises epoxy resin.

Claim 26 (canceled).

Claim 27 (currently amended): A method according to claim [26] 9, wherein said passivation layer is deposited directly onto said layer of material with a work function less than 4 eV.

Claim 28 (canceled).

Claim 29 (currently amended): A method according to claim [28] <u>9</u>, wherein said encapsulating layer comprises a dielectric oxide selected from a group consisting of Al₂O₃, SiO₂, TiO₂, ZrO₂, MgO, HfO₂, Ta₂O₅, aluminum titanium oxide, and tantalum hafnium oxide.

Claim 30 (currently amended): A method according to claim [28] <u>9</u>, wherein said encapsulating layer is deposited by electron beam evaporation.

Claim 31 (currently amended): A method according to claim [28] <u>9</u>, wherein said encapsulating layer is deposited by sputtering.

Claim 32 (previously presented): A method according to claim 9, further comprising the step of sealing the device with an adhesive and glass.

Claim 33 (previously presented): A method according to claim 9, comprising the step of adapting the thickness of said passivation layer to energy of electrons, ions, or fields from which protection is required.

Claim 34 (new): A device according to claim 1, wherein said passivation layer consists of boron oxide and provides a function of absorbing electrons, ions, and electric fields harmful to said transparent cathode thereby protecting said transparent cathode.

Claim 35 (new): A device according to claim 34, further comprising sealing layers of adhesive and glass, and wherein said encapsulating layer comprises a dielectric oxide selected from a group consisting of Al₂O₃, SiO₂, TiO₂, ZrO₂, MgO, HfO₂, Ta₂O₅, aluminum titanium oxide, and tantalum hafnium oxide.

Claim 36 (new): A device according to claim 35, wherein said material with a work function of less than 4 eV comprises calcium, and wherein said light emitting material is a polymeric light emitting material.

Claim 37 (new): A passivation layer according to claim 19, wherein said passivation layer consists of boron oxide for absorbing electrons, ions, and electric fields harmful to the electronic device.